

Very-Low-Power Two-Output PCIe Clock Buffer With On-Chip Termination

Features

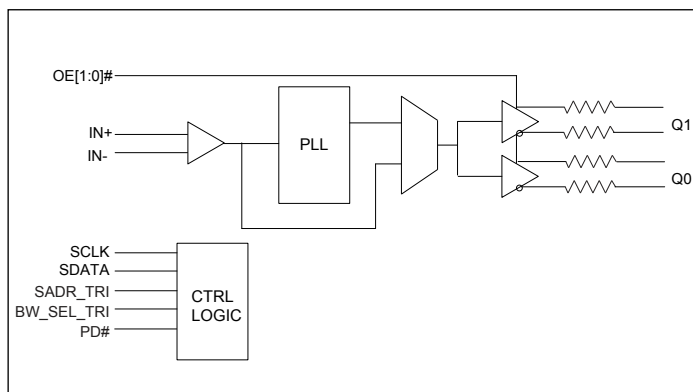
- 3.3V Supply Voltage
- HCSL Input: 100MHz; Also supports 50MHz, 125MHz, or 133.33MHz via SMBus
- Two Differential Low-Power HCSL Outputs with On-Chip Termination
- Default $Z_{OUT} = 85\Omega$
- Spread Spectrum Tolerant
- Individual Output Enable
- Programmable Slew Rate and Output Amplitude for Each Output
- Differential Outputs Blocked until PLL is Locked
- Strapping Pins or SMBus for Configuration
- Differential output-to-output skew <50ps
- Very low jitter outputs
 - Differential cycle-to-cycle jitter <50ps
 - PCIe Gen1/Gen2/Gen3/Gen4/Gen5 CC compliant
 - PCIe Gen 2 and 3 SRiS and SRnS compliant
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. “Green” Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.
- Packaging (Pb-free & Green):
 - 24-lead 4mm × 4mm TQFN

Description

The PI6CB33202 is a two-output very-low-power PCIe Gen1/Gen2/Gen3/Gen4/Gen5 clock buffer. It takes a reference input to fan out two 100MHz low-power differential HCSL outputs with on-chip terminations. The on-chip termination can save eight external resistors and make layout easier. Individual OE pin for each output provides easier power management.

It uses Diodes proprietary PLL design to achieve very-low jitter that meets PCIe Gen1/Gen2/Gen3/Gen4/Gen5 requirements. Other than PCIe 100MHz support, this device also support Ethernet application with 50MHz, 125MHz, and 133.33MHz via SMBus. It provides various options such as different slew rate and amplitude through SMBUS, so users can configure the device easily to get the optimized performance for their individual boards.

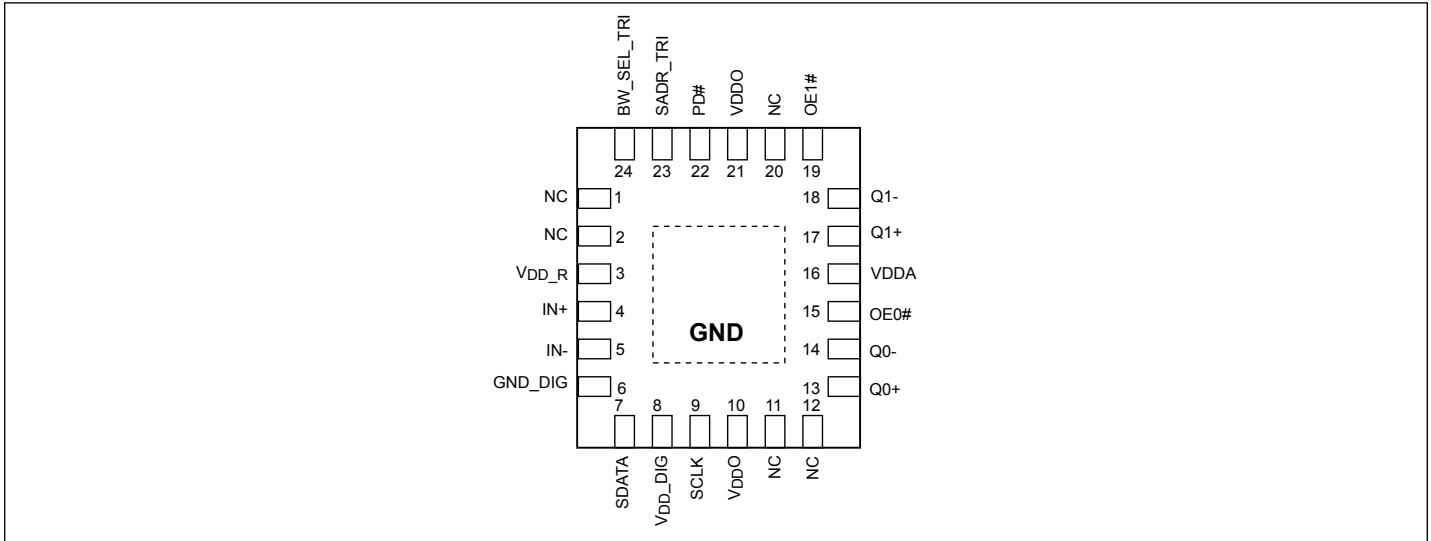
Block Diagram



Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, “Green” and Lead-free.
3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Configuration



Pin Description

Pin Number	Pin Name	Type		Description
1	NC	—	—	Internal connected for feedback loop. Do not connect this pin.
2	NC	—	—	Internal connected for feedback loop. Do not connect this pin.
3	VDD_R	Power	—	Power supply for input differential buffers
4	IN+	Input	—	Differential true clock input
5	IN-	Input	—	Differential complementary clock input
6	GND_DIG	Power	—	Ground for digital circuitry
7	SDATA	Input/ Output	CMOS	SMBUS data line, 3.3V tolerant
8	VDD_DIG	Power	—	Power supply for digital circuitry, nominal 3.3V
9	SCLK	Input	CMOS	SMBUS clock input, 3.3V tolerant
10	VDDO	Power	—	Power supply for differential outputs
11	NC	—	—	Do not connect this pin.
12	NC	—	—	Do not connect this pin.
13	Q0+	Output	HCSL	Differential true clock output
14	Q0-	Output	HCSL	Differential complementary clock output
15	OE0#	Input	CMOS	Active-low input for enabling Q0 pair. This pin has an internal pulldown. 1 =disable outputs, 0 = enable outputs
16	VDDA	Power	—	Power supply for analog circuitry
17	Q1+	Output	HCSL	Differential true clock output

Pin Description Cont.

Pin Number	Pin Name	Type		Description
18	Q1-	Output	HCSL	Differential complementary clock output
19	OE1#	Input	CMOS	Active low input for enabling Q1 pair. This pin has an internal pulldown. 1 =disable outputs, 0 = enable outputs
20	NC	—	—	Do not connect this pin.
21	V _{DDO}	Power	—	Power supply for differential outputs
22	PD#	Input	CMOS	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal pullup resistor.
23	SADR_TRI	Input	Tri-level	Latch to select SMBus Address. This pin has an internal pulldown.
24	BW_SEL_TRI	Input	Tri-level	Latch to select low-loop bandwidth, bypass PLL, and high-loop bandwidth. This pin has both internal pullup and pulldown.
	EPAD	Power	—	Connect to ground.

PI6CB33202

SMBus Address Selection Table

	SADR	Address	+Read/Write Bit
State of SADR on First Application of PD#	0	1101011	X
	M	1101100	X
	1	1101101	X

Power Management Table⁽¹⁾

PD#	IN	SMBus OE bit	OEn#	Qn+	Qn-	PLL Status
0	X	X	X	Low ⁽²⁾	Low ⁽²⁾	Off
1	Running	0	X	Low ⁽²⁾	Low ⁽²⁾	On ⁽¹⁾
1	Running	1	0	Running	Running	On ⁽¹⁾
1	Running	1	1	Low ⁽²⁾	Low ⁽²⁾	On ⁽¹⁾

Note:

1. If PLL Bypass mode is selected, the PLL will be off and outputs will be running.
2. The output state is set by B11[1:0] (Low/Low default).

PLL Operating Mode Select Table

BW_SEL_TRI	Operating Mode	Byte1 [7:6] Readback	Byte1 [4:3] Control
0	PLL with Low Bandwidth	00	00
M	PLL Bypass	01	01
1	PLL with High Bandwidth	11	11

Frequency Select Table

Freq. Select Byte 3 [4:3]	IN (MHz)	Qn (MHz)
00 (default)	100	100
01	50	50
10	125	125
11	133.33	133.33

Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature.....	-65°C to +150°C
Supply Voltage to Ground Potential, V_{DDxx}	-0.5V to +4.6V
Input Voltage	-0.5V to $V_{DD}+0.5V$, not exceed 4.6V
SMBus, Input High Voltage	3.6V
ESD Protection (HBM)	2000 V
Junction Temperature	125°C max

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Operating Conditions

Temperature = T_A ; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V_{DDO} , V_{DDA} , V_{DD_R} , V_{DD_DIG}	Power Supply Voltage	—	3.135	3.3	3.465	V
I_{DDA}	Analog Power Supply Current	V_{DDA} , PLL mode, All outputs active @100MHz	—	21	25	mA
I_{DD_DIG}	Digital Power Supply Current	V_{DD_DIG} , All outputs active @ 100MHz	—	0.1	1	mA
I_{DDO+R}	Power Supply Current for Inputs and Outputs ⁽²⁾	$V_{DDO} + V_{DD_R}$, PLL mode, All outputs active @ 100MHz	—	38	44	mA
I_{DDA_PD}	Analog Power Supply Power Down ⁽¹⁾ Current	V_{DDA} , PLL mode, All outputs LOW/LOW	—	0.5	1	mA
$I_{DD_DIG_PD}$	Power Supply Power Down ⁽¹⁾ Current	V_{DD_DIG} , All outputs LOW/LOW	—	0.1	1	mA
$I_{DDO_R_PD}$	Power Supply Current Power Down ⁽¹⁾ for Inputs and Outputs	V_{DDO} , V_{DD_R} All outputs LOW/LOW	—	1	2	mA
T_A	Ambient Temperature	Industrial grade	-40	—	85	°C

Note:

1. Input clock is not running.
2. Outputs drive 5 inch trace.

Input Electrical Characteristics

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
R_{pu}	Internal Pullup Resistance	—	—	120	—	kΩ
R_{dn}	Internal Pulldown Resistance	—	—	120	—	kΩ
L_{PIN}	Pin Inductance	—	—	—	7	nH

SMBus Electrical Characteristics

Temperature = T_A ; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V_{DDSMB}	Nominal bus voltage	—	2.7	—	3.6	V
V_{IHSMB}	SMBus Input High Voltage	SMBus, $V_{DDSMB} = 3.3V$	2.1	—	3.6	V
		SMBus, $V_{DDSMB} < 3.3V$	0.65 V_{DDSMB}	—	—	
V_{ILSMB}	SMBus Input Low Voltage	SMBus, $V_{DDSMB} = 3.3V$	—	—	0.8	V
		SMBus, $V_{DDSMB} < 3.3V$	—	—	0.8	
$I_{SMBSINK}$	SMBus Sink Current	SMBus, at V_{OLSMB}	4	—	—	mA
V_{OLSMB}	SMBus Output Low Voltage	SMBus, at $I_{SMBSINK}$	—	—	0.4	V
f_{MAXSMB}	SMBus Operating Frequency	Maximum frequency	—	—	500	kHz
t_{RMSB}	SMBus Rise Time	(Max $V_{IL} - 0.15$) to (Min $V_{IH} + 0.15$)	—	—	1000	ns
t_{FMSB}	SMBus Fall Time	(Min $V_{IH} + 0.15$) to (Max $V_{IL} - 0.15$)	—	—	300	ns

LVC MOS DC Electrical Characteristics

Temperature = T_A ; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V_{IH}	Input High Voltage	Single-ended inputs, except SMBus	0.75 V_{DD}	—	V_{DD} +0.3	V
V_{IM}	Input Mid Voltage	SADR_TRI, BW_SEL_TRI	$0.4V_{DD}$	$0.5V_{DD}$	$0.6V_{DD}$	V
V_{IL}	Input Low Voltage	Single-ended inputs, except SMBus	-0.3	—	0.25 V_{DD}	V
I_{IH}	Input High Current	Single-ended inputs, $V_{IN} = V_{DD}$	—	—	5	μA
I_{IL}	Input Low Current	Single-ended inputs, $V_{IN} = 0V$	-5	—	—	μA
I_{IH}	Input High Current	Single-ended inputs with pullup/pulldown resistor, $V_{IN} = V_{DD}$	—	—	50	μA
I_{IL}	Input Low Current	Single-ended inputs with pullup/pulldown resistor, $V_{IN} = 0V$	-50	—	—	μA
C_{IN}	Input Capacitance	—	1.5	—	5	pF

LVC MOS AC Electrical Characteristics

Temperature = T_A ; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
t_{OELAT}	Output Enable Latency	Q start after OE# assertion Q stop after OE# de-assertion	1	—	3	clocks
t_{PDLAT}	PD# De-assertion	Differential outputs enable after PD# de-assertion	—	20	300	μ s

HCSL Input Characteristics⁽¹⁾

Temperature = T_A ; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V_{IHDIF}	Diff. Input High Voltage ⁽³⁾	IN+, IN-, single-end measurement	600	800	1150	mV
V_{ILDIF}	Diff. Input Low Voltage ⁽³⁾	IN+, IN-, single-end measurement	-300	0	300	mV
V_{COM}	Diff. Input Common Mode Voltage		150		900	mV
V_{SWING}	Diff. Input Swing Voltage	Peak to peak value ($V_{IHDIF} - V_{ILDIF}$)	300		2900	mV
f_{INBP}	Input Frequency	PLL Bypass mode	1		200	MHz
f_{IN100}	Input Frequency	100MHz PLL	99.9	100	100.1	MHz
f_{IN133}	Input Frequency	133MHz PLL	133.2	133.33	133.46	MHz
f_{IN125}	Input Frequency	125MHz PLL	124.87	125	125.12	MHz
f_{IN50}	Input Frequency	50MHz PLL	49.95	50	50.05	MHz
$f_{MODI-PCIe}$	Input SS Modulation Freq. PCIe	Allowable frequency for PCIe applications (Triangular Modulation)	30		33	kHz
$f_{MODIN-non-PCIe}$	Input SS Modulation Freq. non-PCIe	Allowable frequency for non-PCIe applications (Triangular Modulation)	0		46	kHz
t_{STAB}	Clock stabilization	From V_{DD} Power-Up and after input clock stabilization or de-assertion of PD# to 1st clock		0.75	1.0	ms
t_{RF}	Diff. Input Slew Rate ⁽²⁾	Measured differentially	0.4			V/ns
I_{IN}	Diff. Input Leakage Current	$V_{IN} = V_{DD}, V_{IN} = GND$	-5	0.01	5	μ A
t_{DC}	Diff. Input Duty Cycle	Measured differentially	45		55	%
t_{j-c-c}	Diff. Input Cycle to cycle jitter	Measured differentially			125	ps

Note:

- Guaranteed by design and characterization, not 100% tested in production
- Slew rate measured through +/-75mV window centered around differential zero
- The device can be driven by a single-ended clock by driving the true clock and biasing the complement clock input to the V_{bias} , where V_{bias} is $(V_{IH} - V_{IL})/2$

HCSL Output Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Typ.	Max.	Units
V _{OH}	Output Voltage High ⁽¹⁾	Statistical measurement on single-ended signal using oscilloscope math function	660	784	850	mV
V _{OL}	Output Voltage Low ⁽¹⁾		-150	—	150	mV
V _{OMAX}	Output Voltage Maximum ⁽¹⁾	Measurement on single ended signal using absolute value	—	816	1150	mV
V _{OMIN}	Output Voltage Minimum ⁽¹⁾		-300	-42	—	mV
V _{OC}	Output Cross Voltage ^(1,2,4)	—	250	430	550	mV
DV _{OC}	V _{OC} Magnitude Change ^(1,2,5)	—	—	12	140	mV

Note:

1. At default SMBUS amplitude settings.
2. Guaranteed by design and characterization—not 100% tested in production.
3. Measured from differential waveform.
4. This one is defined as voltage where Q+ = Q- measured on a component test board and only applied to the differential rising edge.
5. The total variation of all V_{cross} measurements in any particular system. This is a subset of V_{cross_min/max} allowed.

HCSL Output AC Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Typ.	Max.	Units
f _{OUT}	Output Frequency	—	50	100	133.33	MHz
BW	PLL Bandwidth ^(1,8)	-3dB point in High-Bandwidth Mode	1.3	3.2	3.6	MHz
		-3dB point in Low-Bandwidth Mode	0.7	1.7	1.9	MHz
t _{jpeak}	PLL Jitter Peaking ⁽¹⁾	Peak pass band gain	—	0.8	2	dB
t _{RF}	Slew Rate ^(1,2,3)	Scope averaging on fast setting	2.5	3.2	4.0	V/ns
		Scope averaging on slow setting	2.2	3.0	3.7	V/ns
D _{tRF}	Slew Rate Matching ^(1,2,4)	Scope averaging on	—	7	15	%
t _{sKEW}	Output Skew ^(1,2)	Averaging on, V _T = 50%	—	11	50	ps
t _{pDELAY}	Propagation Delay	PLL Bypass mode, V _T = 50%	2000	2500	3000	ps
		PLL mode, V _T = 50%	-200	90	200	ps
t _{DC}	Duty Cycle ^(1,2)	Measured differentially, PLL Mode	45	50	55	%
t _{D_{CD}}	Duty Cycle Distortion ^(1,7)	Measured differentially, PLL Bypass Mode at 100MHz	-3.5	0	3.5	%
t _{D_{CD}}	Duty Cycle Distortion ^(1,7)	Measured differentially, SE input, PLL Bypass Mode at 100MHz	-10	0	10	%
t _{j_{c-c}}	Cycle-to-Cycle Jitter ^(1,2)	PLL mode	—	14	50	ps
		Additive jitter, Bypass mode	—	0.1	1	ps

HCSL Output AC Characteristics (Jitter)

Symbol	Parameters	Condition	Min.	Typ.	Max.	Spec Limit	Units
t _{JPHASEPLL}	Integrated Phase Jitter PLL Mode (RMS) ^(1,5)	PCIe Gen 1 ⁽⁶⁾	—	25	35	86	ps(p-p)
		PCIe Gen 2 Low Band, 10kHz < f < 1.5MHz	—	0.6	0.8	3	ps
		PCIe Gen 2 High Band, 1.5MHz < f < Nyquist (50MHz)	—	0.7	1.2	3.1	ps
		PCIe Gen 3 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)	—	0.25	0.4	1	ps
		PCIe Gen 4 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)	—	0.25	0.4	0.5	ps
		PCIe Gen 5 ⁽¹¹⁾ (PLL BW of 500k to 1.8MHz. CDR =20MHz)	—	0.07	0.12	0.15	ps
		125MHz, 1.5MHz to 20MHz, -20dB/decade Rollover < 1.5MHz, -40dB/decade rolloff > 10MHz	—	0.15	0.3	—	ps
		133.33MHz	—	0.15	0.3	—	ps
t _{JPHASEA}	Additive Integrated Phase Jitter (RMS) ^(1,5,10)	PCIe Gen 1	—	0.01	0.05	—	ps(p-p)
		PCIe Gen 2 Low Band, 10kHz < f < 1.5MHz	—	0.01	0.05	—	ps
		PCIe Gen 2 High Band, 1.5MHz < f < Nyquist (50MHz)	—	0.01	0.05	—	ps
		PCIe Gen 3 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)	—	0.01	0.05	—	ps
		PCIe Gen 4 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)	—	0.01	0.05	—	ps
		PCIe Gen 5 ⁽¹¹⁾ (PLL BW of 500k to 1.8MHz. CDR =20MHz)	—	0.01	0.05	—	ps
		125MHz, 1.5MHz to 20MHz, -20dB/decade Rollover < 1.5MHz, -40dB/decade rolloff > 10MHz	—	0.01	0.05	—	ps
		133.33MHz	—	0.01	0.05	—	ps
		156.25MHz 12k to 20MHz	—	0.01	0.05	—	ps

Note:

1. Guaranteed by design and characterization—not 100% tested in production.
2. Measured from differential waveform.
3. Slew rate is measured through the Vswing voltage range centered around differential 0V, within ±150mV window.
4. Slew rate matching is measured through ±75mV window centered around differential zero.
5. See <http://www.pcisig.com> for complete specs.
6. Sample size of at least 100k cycles. This can be extrapolated to 108ps pk-pk @ 1M cycles for a BER of 10⁻¹².
7. Duty cycle distortion is the difference in duty cycle between the output and input clock when the device is operated in the PLL bypass mode.
8. The minimum and maximum values of each BW setting track each other, low BW maximum will never occur with high BW minimum.
9. Applies to all differential outputs.
10. For additive jitter RMS value is calculated by the following equation = SQRT [(total jitter)^{*2} - (input jitter)^{*2}].
11. PCIe Gen 5 v0.9 specification.

SMBus Serial Data Interface

PI6CB33202 is a slave-only device that supports block-read and block-write protocol using a single 7-bit address and read/write bit as shown below.

Read and write block transfers can be stopped after any complete byte transfer.

Address Assignment

A6	A5	A4	A3	A2	A1	A0	R/W
1	1	0	1	See SBMbus Address Selection table			1/0

Note: SMBus address is latched on SADR pin

How to Write

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit		8 bits	1 bit	1 bit
Start bit	Add.	W(0)	Ack	Beginning Byte location = N	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack	Data Byte (N+X-1)	Ack	Stop bit

How to Read

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit
Start bit	Address	W(0)	Ack	Beginning Byte location = N	Ack	Repeat Start bit	Address	R(1)	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack

											8 bits	1 bit	1 bit
.....											Data Byte (N+X-1)	NAck	Stop bit

Byte 0: Output Enable Register

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	Reserved	—	—	0	See B11[1:0]	Pin control
6	Reserved	—	—	0		
5	Reserved	—	—	0		
4	Q1_OE	Q1 output enable	RW	1		
3	Q0_OE	Q0 output enable	RW	1		
2	Reserved	—	—	0		
1	Reserved	—	—	0		
0	Reserved	—	—	0		

Note:

1. A low on these bits will override the OE# pins and force the differential outputs to the state indicated by B11[1:0] (Low/Low default).

Byte 1: PLL Operating Mode and Output Amplitude Control Register

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	PLLMODERB1	PLL Mode Readback Bit1	R	Latch	See PLL Operating Mode Table	
6	PLLMODERB0	PLL Mode Readback Bit0	R	Latch		
5	PLLMODE_SWCTR	Enable SW control of PLL Mode	RW	0	Values in B1[7:6] set PLL Mode	Values in B1[4:3] set PLL Mode
4	PLLMODE1	PLL Mode control Bit1	RW ⁽¹⁾	0	See PLL Operating Mode Table	
3	PLLMODE0	PLL Mode control Bit0	RW ⁽¹⁾	0		
2	Reserved	—	—	1	—	—
1	Amplitude1	Control output amplitude	RW	1	'00' = 0.6V, '01' = 0.68V, '10' = 0.75V, '11' = 0.85V	
0	Amplitude0		RW	0		

Note:

1. B1[5] must be set to a 1 for these bits to have any effect on the part.

Byte 2: Differential Output Slew Rate Control Register

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	Reserved	—	—	1	—	—
6	Reserved	—	—	1	—	—
5	Reserved	—	—	1	—	—
4	SLEWRATECTR_Q1	Control slew rate of Q1	RW	1	Slow setting	Fast setting
3	SLEWRATECTR_Q0	Control slew rate of Q0	RW	1	Slow setting	Fast setting
2	Reserved	—	—	1	—	—
1	Reserved	—	—	1	—	—
0	Reserved	—	—	1	—	—

Byte 3: Frequency Select Control Register

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	Reserved	—	—	1	—	—
6	Reserved	—	—	1	—	—
5	FREQ_SEL_EN	Enable SW selection of frequency	RW	0	SW Freq. selection disabled	SW Freq. selection enabled
4	FSEL1	Freq. Select Bit 1	RW ⁽¹⁾	0	See Frequency Select Table	
3	FSEL0	Freq. Select Bit 0	RW ⁽¹⁾	0		
2	Reserved	—	—	1	—	—
1	Reserved	—	—	1	—	—
0	SLEWRATESEL_FB	Adjust Slew Rate of Feedback signal	RW	1	Slow setting	Fast setting

Note:

1. B3[5] must be set to a 1 for these bits to have any effect on the part.

Byte 4: Reserved

Bit	Control Function	Description	Type	Power-up Condition	0	1
7:0	Reserved	—	—	1	—	—

Byte 5: Revision and Vendor ID Register

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	RID3	Revision ID	R	0	rev = 0000	
6	RID2		R	0		
5	RID1		R	0		
4	RID0		R	0		
3	PVID3	Vendor ID	R	0	Diodes = 0011	
2	PVID2		R	0		
1	PVID1		R	1		
0	PVID0		R	1		

Byte 6: Device Type/Device ID Register

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	DTYPE1	Device type	RW	0	'00' = CG, '01' = ZDB, '10' = Reserve, '11' = ZDB	
6	DTYPE0		RW	1		
5	DID5	Device ID	RW	0	000010 binary, 02Hex	
4	DID4		RW	0		
3	DID3		RW	0		
2	DID2		RW	0		
1	DID1		RW	1		
0	DID0		RW	0		

Byte 7: Reserved

Bit	Control Function	Description	Type	Power-up Condition	0	1
7:0	Reserved	—	—	0x08	—	—

Byte 8 and 9: Reserved

Bit	Control Function	Description	Type	Power-up Condition	0	1
7:0	Reserved	—	—	B8 = 0x36 B9 = 0x00	—	—

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Byte 10: PD Restore

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	Reserved	—	RW	1	—	—
6	PD Restore	PD Restore to default configuration	RW	1	Clear PD Config	Keep PD Config
5:0	Reserved	—	R	0	—	—

Byte 11: Stop Control

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	FB_imp[1]	Feedback Zout	RW	0	00=Reserved	10=100 DIF Zout
6	FB_imp[0]		RW	1	01=85 DIF Zout	11 = Reserved
5:2	Reserved	—	—	0	—	—
1	STP1	True/ Compliment DIF Output Disable Sate	RW	0	00= Low/Low	10= High/Low
0	STP0		RW	0	01= HiZ/HiZ	11= Low/High

Byte 12: Impedance Control

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	Q0_Zout1	Q0 Zout	RW	01	00 = Reserved 01 = 85Ω 10 = 100Ω 11 = Reserved	
6	Q0_Zout0	Q0 Zout	RW			
5	Reserved	—	RW			
4	Reserved	—	RW			
3	Reserved	—	RW			
2	Reserved	—	RW			
1	Reserved	—	RW			
0	Reserved	—	RW			

Byte 13: Impedance Control

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	Reserved	—	RW	01	00 = Reserved 01 = 85Ω 10 = 100Ω 11 = Reserved	
6	Reserved	—	RW			
5	Reserved	—	RW			
4	Reserved	—	RW			
3	Reserved	—	RW			
2	Reserved	—	RW			
1	Q1_Zout1	Q1 Zout	RW			
0	Q1_Zout0	Q1 Zout	RW			

Byte 14: OE Termination Control

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	OE0_term1	OE0 Pullup or down	RW	0	00=None	10= Pullup
6	OE0_term0	OE0 Pullup or down	RW	1	01= Pulldown	11=Pullup and Down
5	Reserved	—	RW	0	—	—
4	Reserved	—	RW	1	—	—
3	Reserved	—	RW	0	—	—
2	Reserved	—	RW	1	—	—
1	Reserved	—	—	0	—	—
0	Reserved	—	—	1	—	—

Byte 15: OE Termination Control

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	Reserved	—	RW	0	—	—
6	Reserved	—	RW	1	—	—
5	Reserved	—	RW	0	—	—
4	Reserved	—	RW	1	—	—
3	Reserved	—	—	0	—	—
2	Reserved	—	—	1	—	—
1	OE1_term1	OE1 Pullup or down	RW	0	00=None	10= Pullup
0	OE1_term0	OE1 Pullup or down	RW	1	01= Pulldown	11=Pullup and Down

Byte 16: Power Good Termination Control

Bit	Control Function	Description	Type	Power-up Condition	0	1
7:2	Reserved	—	—	0x00	—	—
1	PWRGD_PD1	Clock Power Good and Power Down Pull up or Pull down	RW	1	00=None	10= Pullup
0	PWRGD_PD0		RW	0	01= Pulldown	11=Pullup and Down

Byte 17: Reserved

Bit	Control Function	Description	Type	Power-up Condition	0	1
7:0	Reserved	—	—	0	—	—

Byte 18: Enable Pin Control

Bit	Control Function	Description	Type	Power-up Condition	0	1
7	Reserved	—	RW	0	—	—
6	Reserved	—	RW	0	—	—
5	Reserved	—	—	0	—	—
4	OE1_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
3	OE0_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
2	Reserved	—	RW	0	—	—
1	Reserved	—	RW	0	—	—
0	Reserved	—	RW	0	—	—

Byte 19: Power Down Pin Control

Bit	Control Function	Description	Type	Power-up Condition	0	1
7:1	Reserved	—	—	0	—	—
0	PWRGD_PD	PWRGD_PD Active via Pull up or Pull down	RW	0	Power Down = Low	Power Down = High

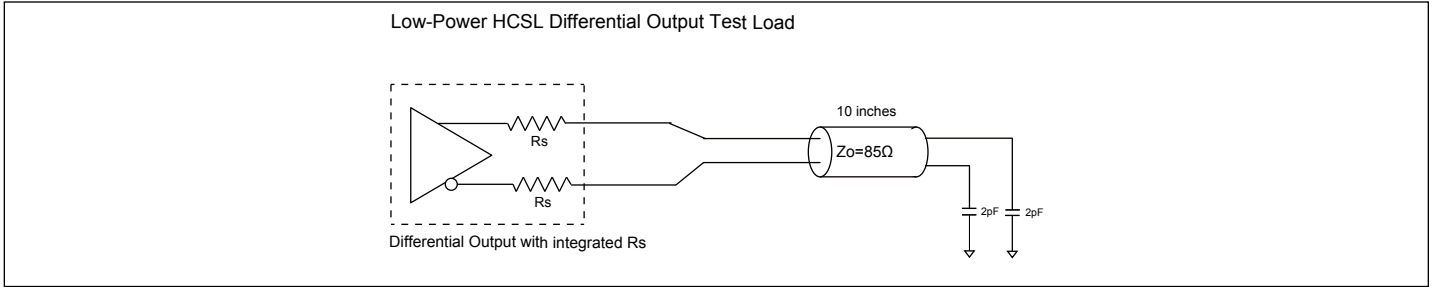


Figure 1. Low-Power HCSL Test Circuit

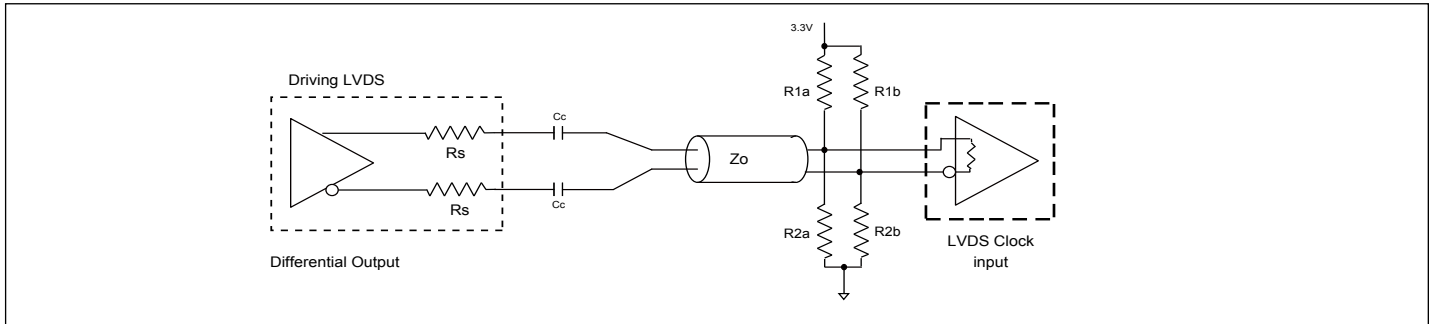


Figure 2. Differential Output Driving LVDS

Alternate Differential Output Terminations ($Z_O = 85\Omega$)

Component	Receiver with Termination	Receiver without Termination	Unit
R _{1a} , R _{1b}	10,000	130	Ω
R _{2a} , R _{2b}	5600	64	Ω
C _C	0.1	0.1	μF
V _{CM}	1.2	1.2	V

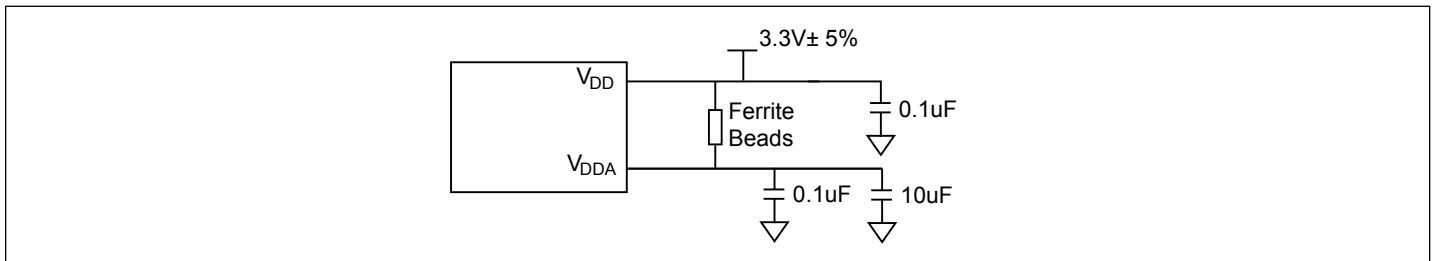


Figure 3. Power Supply Filter

Thermal Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
θ_{JA}	Thermal Resistance Junction to Ambient	Still air			54.4	$^{\circ}\text{C}/\text{W}$
θ_{JC}	Thermal Resistance Junction to Case				40.8	$^{\circ}\text{C}/\text{W}$

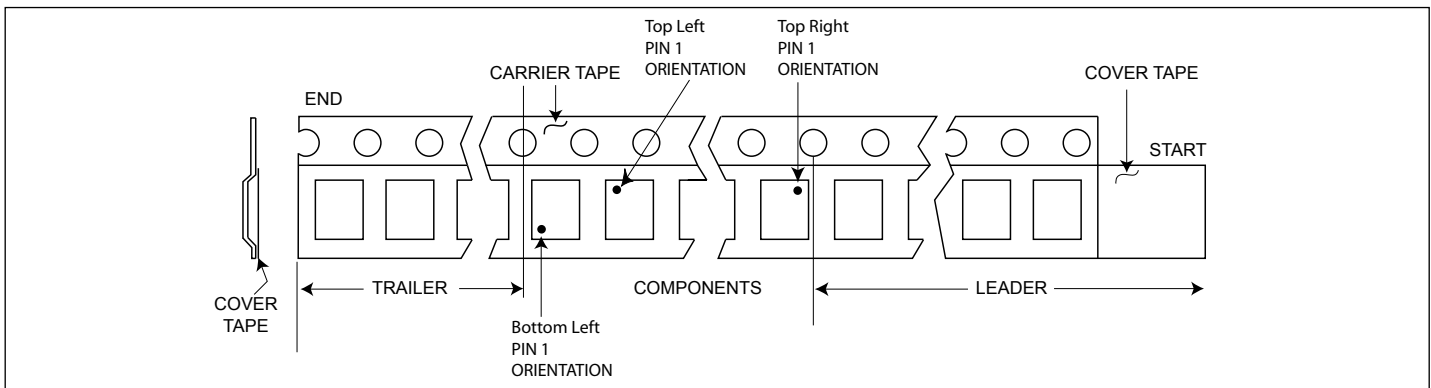
PI6CB33202

Part Marking

PI6CB33
202ZDIE
ZYWXX
○

Z: Die Rev
Y: Year
W: Workweek
1st X: Assembly Code
2nd X: Fab Code

Package Information



Suffix	Tape Orientation
-13R	
-13RA	

PI6CB33202

Packaging Mechanical

24-TQFN (ZD)

SYMBOLS	MIN.	NOM.	MAX.
A	0.80	0.85	0.90
A1	0.00	0.02	0.05
A3	0.20 REF.		
b	0.18	0.25	0.30
D	3.90	4.00	4.10
E	3.90	4.00	4.10
e	0.50 BSC		
D2	2.15	—	2.75
E2	2.15	—	2.75
L	0.35	0.40	0.45

NOTE :

- ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
- COPLANARITY APPLIES TO THE EXPOSED THERMAL PAD AS WELL AS THE TERMINALS.
- REFER JEDEC MO-220
- RECOMMENDED LAND PATTERN IS FOR REFERENCE ONLY.
- THERMAL PAD SOLDERING AREA
- MAJOR EDAP D2XE2=2.25X2.25

DATE: 07/07/17

DESCRIPTION: 24-Contact, Very Thin Quad Flat No-Lead (TQFN)

PACKAGE CODE: ZD (ZD24)

DOCUMENT CONTROL #: PD-2100 **REVISION: C**

17-0533

For latest package information:

See <http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/>.

Ordering Information

Ordering Code	Package Code	Package Description	Pin 1 Location
PI6CB33202ZDIEX	ZD	24-Contact, Very-Thin Quad-Flat No-Lead (TQFN)	Top Right Corner
PI6CB33202ZDIEX-13R	ZD	24-Contact, Very-Thin Quad-Flat No-Lead (TQFN)	Top Left Corner

Notes:

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- E = Pb-free and Green
- X suffix = Tape/Reel
- For packaging details, go to our website at: <https://www.diodes.com/assets/MediaList-Attachments/Diodes-Package-Information.pdf>

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